

**Amendments to the claims**

Please amend the claims as follows.

1-158. (canceled)

159. (new) A method for treating a surface of a substrate having a dielectric material layer disposed thereon and an organic material layer overlying the dielectric layer; the method comprising the steps of:

contacting the surface of the substrate with an aqueous solution comprising a 2:1 (v/v) ratio of hydrofluoric acid and organic acid to provide a pH of about 2-5 and selective removal of the dielectric material to the organic material at an etch rate of about 50:1 to about 1000:1.

160. (new) A method for selective removal of a dielectric layer from a surface of a substrate having the dielectric layer disposed thereon and an organic material layer disposed over the dielectric layer, the method comprising the steps of:

contacting the surface of the substrate with an aqueous solution comprising hydrofluoric acid and organic acid in a ratio of 2:1 (v/v) to provide a pH of about 2-5, and selective removal of the dielectric material to the organic material at a rate greater than about 1000 angstroms per minute and an etch selectivity of about 50:1 to about 1000:1.

161. (new) A method for selective removal of a dielectric layer from a surface of a substrate having the dielectric layer disposed thereon and an organic material layer disposed over the dielectric layer, the method comprising the steps of:

contacting the surface of the substrate with an aqueous solution comprising hydrofluoric acid and organic acid in a ratio of 2:1 (v/v) to provide a pH of about 2-5, selective removal of the dielectric material to the organic material at a rate greater than about 2000 angstroms per minute, and an etch selectivity of about 50:1 to about 1000:1.

162. (new) A method for selective removal of a dielectric layer from a surface of a substrate having the dielectric layer disposed thereon and an organic material layer disposed over the dielectric layer, the method comprising the steps of:

contacting the surface of the substrate with an aqueous solution comprising hydrofluoric acid and organic acid in a ratio of 2:1 (v/v) to provide a pH of about 2-5, and selective removal of the dielectric material to the organic material at a rate greater than about 2300-2700 angstroms per minute and an etch selectivity of about 50:1 to about 1000:1.

163. (new) A method for selective removal of a dielectric layer from a surface of a substrate having the dielectric layer disposed thereon and an organic material layer disposed over the dielectric layer, the method comprising the steps of:

contacting the surface of the substrate with an aqueous solution comprising hydrofluoric acid and organic acid in a ratio of 2:1 (v/v) to provide a pH of about 2-5, such that the dielectric layer is selectively removed at a rate greater than about 1000 angstroms per minute with minimal removal of the organic material layer.

164. (new) A method for selective removal of a dielectric layer from a surface of a substrate having the dielectric layer disposed thereon and an organic material layer disposed over the dielectric layer, the method comprising the steps of:

contacting the surface of the substrate with an about 2:1 (v/v) aqueous solution of an about 49% hydrofluoric acid and an about 50% organic acid to provide a pH of about 2-5, and selective removal of the dielectric material to the organic material at a rate greater than about 2300-2700 angstroms per minute and an etch selectivity of about 50:1 to about 1000:1.

165. (new) A method for selective removal of a dielectric layer from a surface of a substrate having the dielectric layer disposed thereon and an organic material layer disposed over the dielectric layer, the method comprising the steps of:

contacting the surface of the substrate with an aqueous solution comprising an about 63-70 % by volume of hydrofluoric acid and about 30-36 % by volume of organic acid to provide a pH of about 2-5, and selective removal of the dielectric material to the organic material at a rate

greater than about 1000 angstroms per minute and an etch selectivity of about 50:1 to about 1000:1.

166. (new) A method for selective removal of a dielectric layer from a surface of a substrate having the dielectric layer disposed thereon and an organic layer disposed over the dielectric layer, the method comprising the steps of:

preparing an aqueous solution by combining about 63-70 % by volume of an about 49% hydrofluoric acid and about 30-36 % by volume of an about 50% organic acid to provide a pH of about 2-5, and a removal rate of dielectric material of greater than about 1000 angstroms per minute and an etch selectivity of dielectric material to organic material of about 50:1 to about 1000:1 when the solution is applied thereto; and

applying the aqueous solution to the surface of the substrate wherein the dielectric layer is selectively removed at a rate greater than about 1000 angstroms per minute and at an etch selectivity of the dielectric layer to the organic layer of about 50:1 to about 1000:1.

167. (new) A method for selective removal of a dielectric layer from a surface of a substrate having the dielectric layer disposed thereon and an organic layer disposed over the dielectric layer, the method comprising the steps of:

preparing an aqueous solution by combining about 63-70 % by volume of an about 49% hydrofluoric acid and about 30-36 % by volume of an about 50% organic acid to provide a pH of about 3-6;

applying the aqueous solution to the surface of the substrate wherein the dielectric layer is selectively removed at a rate greater than about 1000 angstroms per minute, and an etch selectivity of the dielectric layer to the organic layer of about 50:1 to about 1000:1.

168. (new) A method for selective removal of a dielectric layer from a surface of a substrate having the dielectric layer disposed thereon and an organic layer disposed over the dielectric layer, the method comprising the steps of:

preparing an aqueous solution by combining about 63-70 % by volume of an about 49% hydrofluoric acid and about 30-36 % by volume of an about 50% organic acid,

adjusting the amount of organic acid in the solution to a pH of about 3-6 such that the removal rate of the dielectric layer is greater than about 1000 angstroms; and

applying the aqueous solution to the surface of the substrate wherein the dielectric layer is selectively removed at a rate greater than about 1000 angstroms per minute and at an etch selectivity of the dielectric layer to the organic layer of about 50:1 to about 1000:1.

169. (new) The method of Claim 168, wherein the amount of the organic acid is adjusted to provide a pH such that the removal rate of the dielectric layer is greater than about 2000 angstroms per minute.

170. (new) The method of Claim 168, wherein the organic material is removed at a rate of about 1 angstrom per minute.